

# N-channel TrenchMOS intermediate level FET

Rev. 1 — 12 July 2011

Product data sheet

# 1. Product profile

### 1.1 General description

Intermediate level gate drive N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using advanced TrenchMOS technology. This product has been designed and qualified to the appropriate AEC Q101 standard for use in high performance automotive applications.

### 1.2 Features and benefits

- AEC Q101 compliant
- Suitable for standard and logic level gate drive sources

### **1.3 Applications**

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control

### 1.4 Quick reference data

#### Table 1. Quick reference data

- Suitable for thermally demanding environments due to 175 °C rating
- Start-Stop micro-hybrid applications

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- Transmission control
- Ultra high performance power switching

Table 1.	Quick reference uata						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	[1]	-	-	90	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	-	128	W
Static cha	racteristics						
$R_{DSon}$	drain-source on-state resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C; see <u>Figure 11</u>		-	5.2	6.2	mΩ

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Table 1.	Quick reference data	acontinued				
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{array}{l} I_{D} = 90 \text{ A};  \text{V}_{sup} \leq 40 \text{ V}; \\ \text{R}_{\text{GS}} = 50  \Omega;  \text{V}_{\text{GS}} = 10 \text{ V}; \\ \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} \end{array}$	-	-	113	mJ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure } 13}{\text{Figure } 14}$	-	20	-	nC

[1] Continuous current is limited by package.

#### **Pinning information** 2.

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		-
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT428 (DPAK)

#### **Ordering information** 3.

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK626R2-40C	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

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### 4. Limiting values

#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC	<u>[1]</u>	-16	16	V
		Pulsed	[2]	-20	20	V
I <sub>D</sub>	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } \frac{\text{Figure 1}}{10000000000000000000000000000000000$	<u>[3]</u>	-	90	А
		$T_{mb}$ = 100 °C; $V_{GS}$ = 10 V; see <u>Figure 1</u>		-	70	А
I <sub>DM</sub>	peak drain current	T <sub>mb</sub> = 25 °C; pulsed; t <sub>p</sub> ≤ 10 μs; see <u>Figure 3</u>		-	397	Α
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>		-	128	W
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[3]	-	90	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	397	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$    I_D = 90 \text{ A};  \text{V}_{\text{sup}} \leq 40 \text{ V};  \text{R}_{\text{GS}} = 50  \Omega; \\ \text{V}_{\text{GS}} = 10 \text{ V};  \text{T}_{j(\text{init})} = 25 ^{\circ}\text{C}; \text{ unclamped} $		-	113	mJ
E <sub>DS(AL)R</sub>	repetitive drain-source avalanche energy		[4][5][6]	-	-	J

[1] -16V accumulated duration not to exceed 168 hrs.

[2] Accumulated pulse duration not to exceed 5mins.

[3] Continuous current is limited by package.

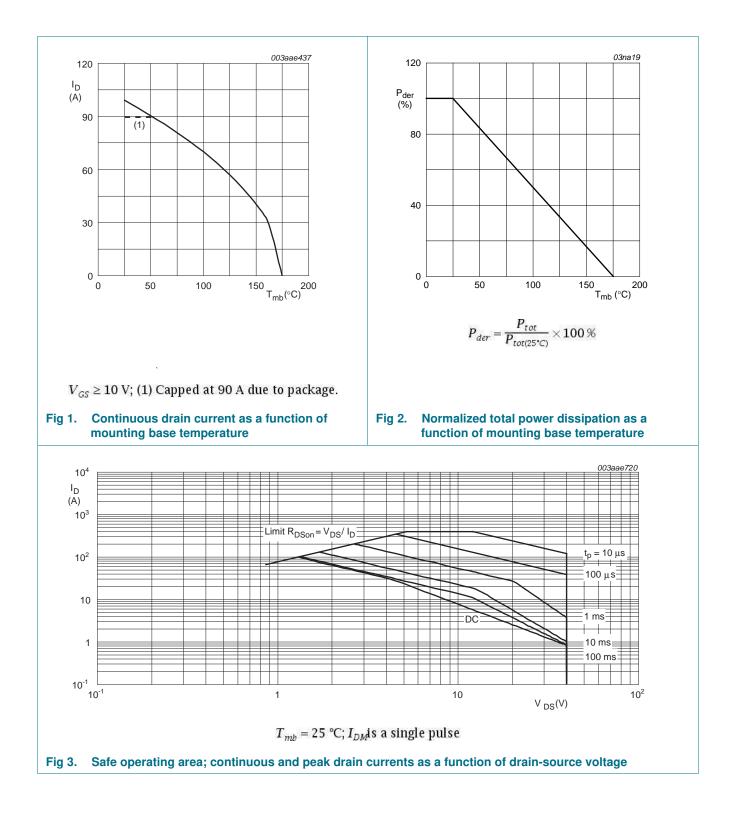
[4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

[5] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[6] Refer to application note AN10273 for further information.

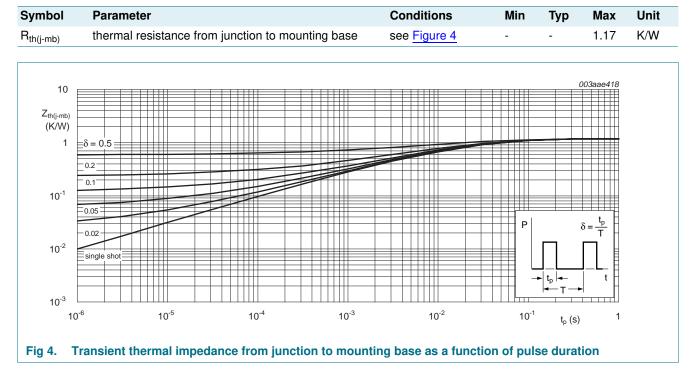
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### 5. Thermal characteristics



#### Table 5. Thermal characteristics

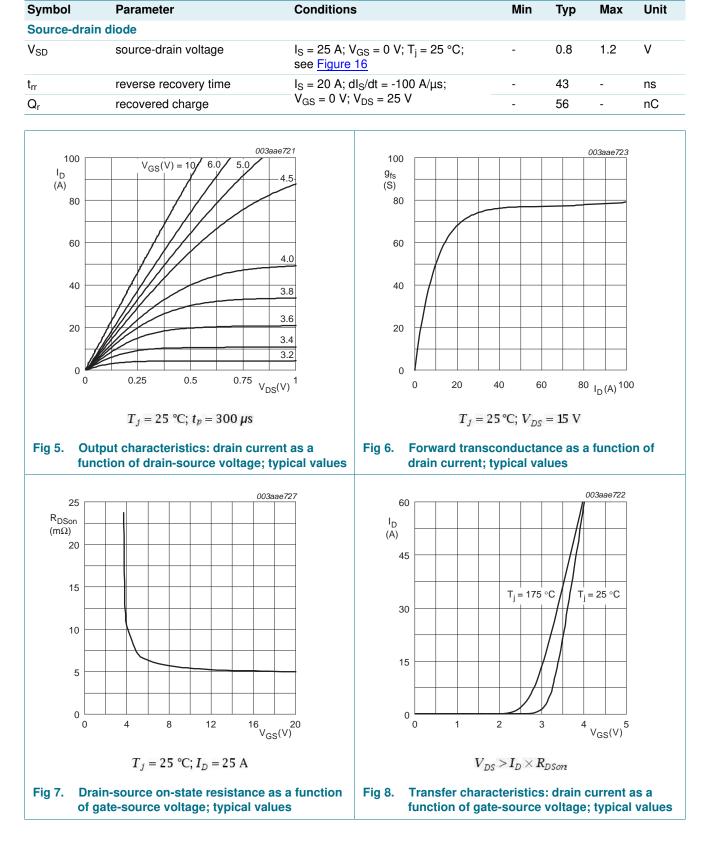
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# 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ\text{C}$	40	-	-	V
		$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	36	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 9</u> ; see <u>Figure 10</u>	1.8	2.3	2.8	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 9</u>	-	-	3.3	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ see <u>Figure 9</u>	0.8	-	-	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ °C}$	-	-	500	μA
		$V_{DS} = 40 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	0.02	1	μA
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
		$V_{GS}$ = -20 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	2	100	nA
R <sub>DSon</sub> drain-source on-state	drain-source on-state resistance	$\label{eq:VGS} \begin{array}{l} V_{GS} = 10 \; V; \; I_D = 15 \; A; \; T_j = 25 \; ^{\circ}C; \\ see \; \underline{Figure \; 11} \end{array}$	-	5.2	6.2	mΩ
		$V_{GS} = 5 \text{ V}; \text{ I}_D = 15 \text{ A}; \text{ T}_j = 25 \text{ °C};$ see Figure 11	- 7	7	8.8	mΩ
		$V_{GS}$ = 4.5 V; $I_D$ = 15 A; $T_j$ = 25 °C; see <u>Figure 11</u>	-	8	10.7	mΩ
		$V_{GS} = 10 \text{ V}; \text{ I}_D = 15 \text{ A}; \text{ T}_j = 175 \text{ °C};$ see <u>Figure 12</u> ; see <u>Figure 11</u>	-	-	13	mΩ
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub> t	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$ see <u>Figure 13</u> ; see <u>Figure 14</u>	-	67	-	nC
		$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 5 \text{ V};$ see Figure 13; see Figure 14	-	39	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	11	-	nC
Q <sub>GD</sub>	gate-drain charge	see Figure 13; see Figure 14	-	20	-	nC
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;$	-	2790	3720	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; see <u>Figure 15</u>	-	380	456	pF
C <sub>rss</sub>	reverse transfer capacitance		-	275	377	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 30 \ V; R_L = 1.2 \ \Omega; V_{GS} = 10 \ V;$	-	16.7	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega$	-	48.6	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	124	-	ns
t <sub>f</sub>	fall time		-	17	-	ns
L <sub>D</sub>	internal drain inductance	from upper edge of drain mounting base to centre of die ; $T_j = 25 \text{ °C}$	-	3.5	-	nH
L <sub>S</sub>	internal source inductance	from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH

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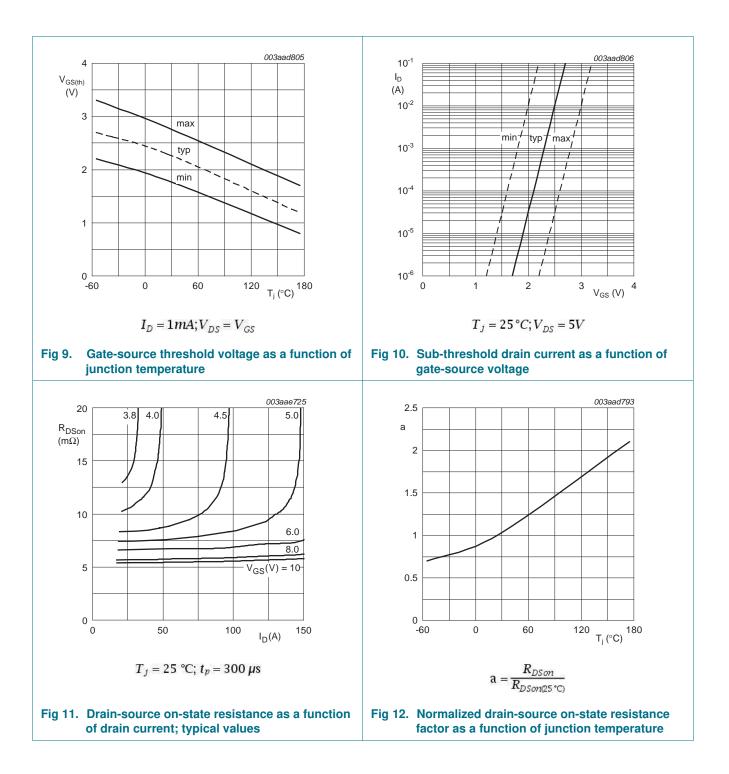


#### Table 6. Characteristics ...continued

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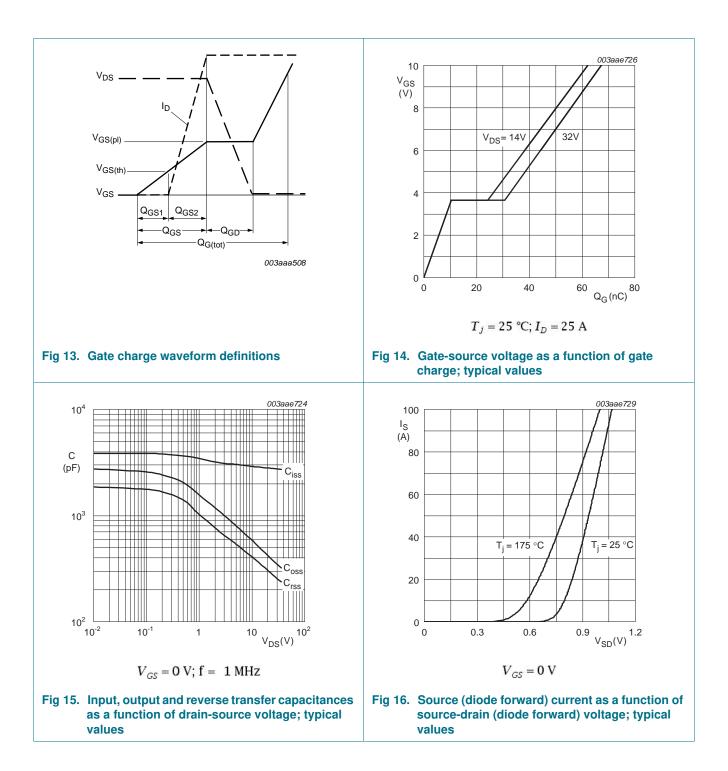
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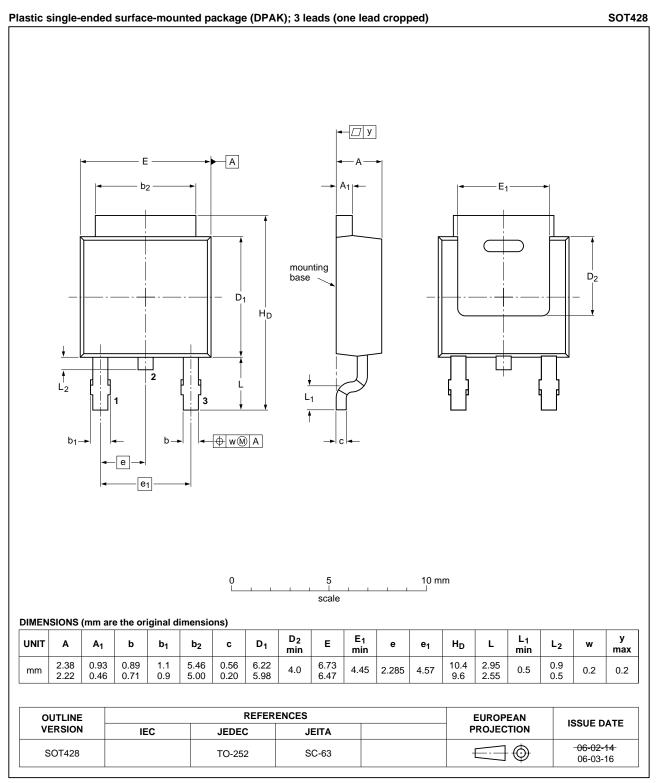
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# 7. Package outline



#### Fig 17. Package outline SOT428 (DPAK)

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# 8. Revision history

Table 7. Revision h	7. Revision history					
Document ID	Release date	Data sheet status	Change notice	Supersedes		
BUK626R2-40C v.1	20110712	Product data sheet	-	-		

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Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".

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